



DMP2160UW

Features

- Low On-Resistance
 - 100 m Ω @ V_{GS} = -4.5V
 - 120 m Ω @ $V_{GS} = -2.5V$
 - 160 m Ω @ $V_{GS} = -1.8V$
- Very Low Gate Threshold Voltage V_{GS(th)} ≤ 1V
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q 101 Standards for High Reliability

Mechanical Data

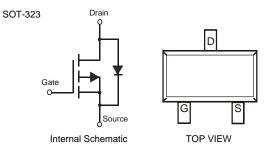
- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0

P-CHANNEL ENHANCEMENT MODE MOSFET

- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.006 grams (approximate)







Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	-20	V
Gate-Source Voltage		V _{GSS}	±12	V
Drain Current (Note 3)	$T_A = 25$ °C $T_A = 70$ °C	I _D	-1.5 -1.2	А
Pulsed Drain Current		I _{DM}	-10	Α

Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 3)	P _D	350	mW
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	360	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- Device mounted on 1in^2 FR-4 PCB with 2 oz. Copper. $t \le 10$ sec.

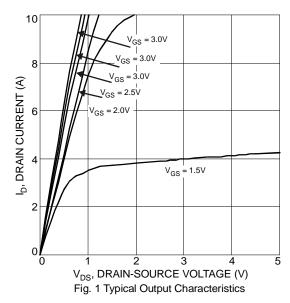


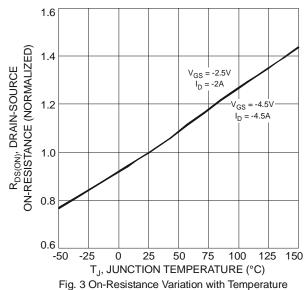
Electrical Characteristics @T_A = 25°C unless otherwise specified

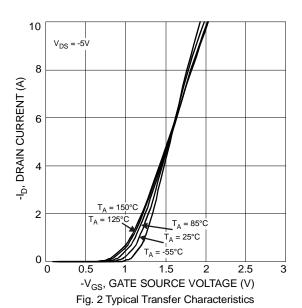
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	_	_	-1.0	μΑ	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±100 ±800	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$ $V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	V _{GS(th)}	-0.4	-0.6	-0.9	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
Static Drain-Source On-Resistance	R _{DS (ON)}	_	75 90 120	100 120 160	mΩ	$V_{GS} = -4.5V, I_D = -1.5A$ $V_{GS} = -2.5V, I_D = -1.2A$ $V_{GS} = -1.8V, I_D = -1A$
Forward Transconductance	g _{FS}	_	4	_	S	$V_{DS} = -10V, I_{D} = -1.5A$
Diode Forward Voltage (Note 4)	V_{SD}		_	-1.0	V	$V_{GS} = 0V, I_{S} = -1.0A$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	_	627	_	pF	101/1/
Output Capacitance	Coss	_	64	_	pF	$V_{DS} = -10V, V_{GS} = 0V$ -f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	53		pF	1 = 1.0ivii iz

Notes:

4. Short duration pulse test used to minimize self-heating effect.



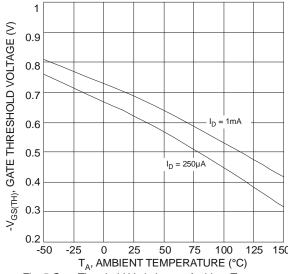




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V_{DS}, DRAIN-SOURCE VOLTAGE (V) Fig. 4 Typical Capacitance





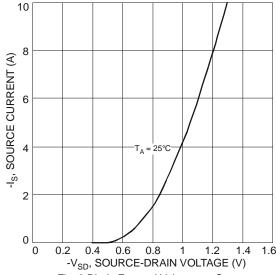
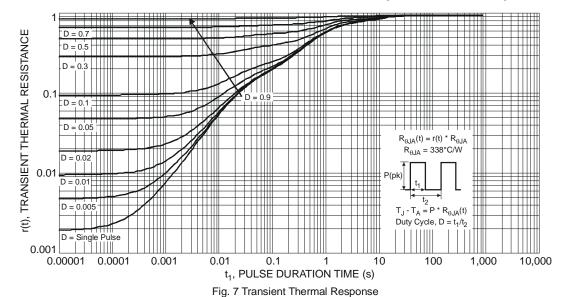


Fig. 5 Gate Threshold Variation vs. Ambient Temperature

Fig. 6 Diode Forward Voltage vs. Current

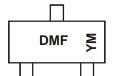


Ordering Information (Note 5)

Part Number	Case	Packaging
DMP2160UW-7	SOT-323	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



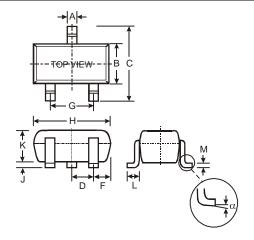
DMF = Marking Code YM = Date Code Marking Y = Year (ex: V = 2008) M = Month (ex: 9 = September)

Date Code Key

Date Code Ney												
Year	2008		2009	2010)	2011	2012	!	2013	2014	l l	2015
Code	V		W	X		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	Mav	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

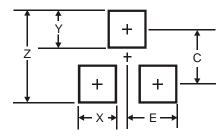


Package Outline Dimensions



	SOT-323						
Dim	Min	Max	Тур				
Α	0.25	0.40	0.30				
В	1.15	1.35	1.30				
С	2.00	2.20	2.10				
D	-	-	0.65				
F	0.30	0.40	0.425				
G	1.20	1.40	1.30				
Н	1.80	2.20	2.15				
J	0.0	0.10	0.05				
K	0.90	1.00	1.00				
L	0.25	0.40	0.30				
М	0.10	0.18	0.11				
α	0°	8°	-				
All	All Dimensions in mm						

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.8
Х	0.7
Y	0.9
С	1.9
E	1.0

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